# Silicon Power Transistors

The MJL21193 and MJL21194 utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

# Features

- Total Harmonic Distortion Characterized
- High DC Current Gain -

 $h_{FE} = 25 \text{ Min} @ I_C$ = 8 Adc

- Excellent Gain Linearity
- High SOA: 2.25 A, 80 V, 1 Second
- These are Pb-Free Devices\*

# **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	250	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	400	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5	Vdc
Collector-Emitter Voltage - 1.5 V	V <sub>CEX</sub>	400	Vdc
Collector Current – Continuous Peak (Note 1)	Ι <sub>C</sub>	16 30	Adc
Base Current – Continuous	Ι <sub>Β</sub>	5	Adc
Total Power Dissipation @ $T_C = 25^{\circ}C$ Derate above $25^{\circ}C$	P <sub>D</sub>	200 1.43	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 65 to + 150	°C

## **THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2%

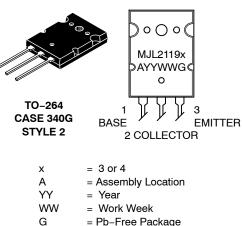


# **ON Semiconductor®**

http://onsemi.com

# **16 AMPERE COMPLEMENTARY** SILICON POWER TRANSISTORS 250 VOLTS, 200 WATTS

**MARKING DIAGRAM** 



## = Pb-Free Package

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MJL21193G	TO-264 (Pb-Free)	25 Units / Rail
MJL21194G	TO-264 (Pb-Free)	25 Units / Rail

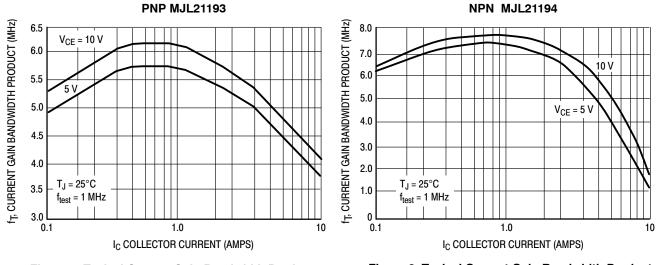
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS		·				
Collector–Emitter Sustaining Voltage $(I_{C} = 100 \text{ mAdc}, I_{B} = 0)$		V <sub>CEO(sus)</sub>	250	-	-	Vdc
Collector Cutoff Current $(V_{CE} = 200 \text{ Vdc}, I_B = 0)$	I <sub>CEO</sub>	-	-	100	μAdc	
Emitter Cutoff Current ( $V_{CE} = 5 \text{ Vdc}, I_C = 0$ )			_	-	100	μAdc
Collector Cutoff Current (V <sub>CE</sub> = 250 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc)	I <sub>CEX</sub>	-	-	100	μAdc	
SECOND BREAKDOWN		•				
Second Breakdown Collector Current with Base For (V <sub>CE</sub> = 50 Vdc, t = 1 s (non-repetitive) (V <sub>CE</sub> = 80 Vdc, t = 1 s (non-repetitive)	I <sub>S/b</sub>	4.0 2.25			Adc	
ON CHARACTERISTICS						
DC Current Gain (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 5 Vdc) (I <sub>C</sub> = 16 Adc, I <sub>B</sub> = 5 Adc)		h <sub>FE</sub>	25 8		75 -	
Base–Emitter On Voltage (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 5 Vdc)	V <sub>BE(on)</sub>	-	-	2.2	Vdc	
Collector–Emitter Saturation Voltage ( $I_C = 8 \text{ Adc}, I_B = 0.8 \text{ Adc}$ ) ( $I_C = 16 \text{ Adc}, I_B = 3.2 \text{ Adc}$ )	V <sub>CE(sat)</sub>			1.4 4	Vdc	
DYNAMIC CHARACTERISTICS		·				
Total Harmonic Distortion at the Output V <sub>RMS</sub> = 28.3 V, f = 1 kHz, P <sub>LOAD</sub> = 100 W <sub>RMS</sub>	h <sub>FE</sub> unmatched	T <sub>HD</sub>		0.8		%
(Matched pair $h_{FE}$ = 50 @ 5 A/5 V)	h <sub>FE</sub> matched		_	0.08	_	
Current Gain Bandwidth Product (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 10 Vdc, $f_{test}$ = 1 MHz)		f <sub>T</sub>	4	-	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)		C <sub>ob</sub>	_	-	500	pF







# **TYPICAL CHARACTERISTICS**

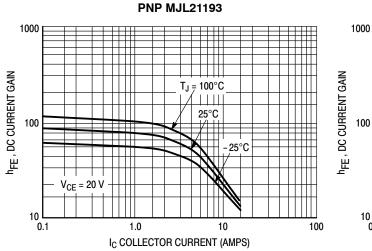
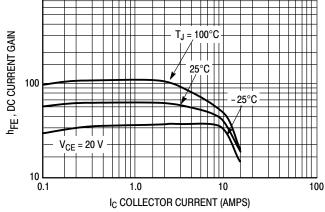


Figure 3. DC Current Gain, V<sub>CE</sub> = 20 V



NPN MJL21194

Figure 4. DC Current Gain, V<sub>CE</sub> = 20 V

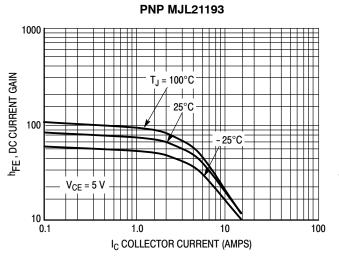


Figure 5. DC Current Gain, V<sub>CE</sub> = 5 V



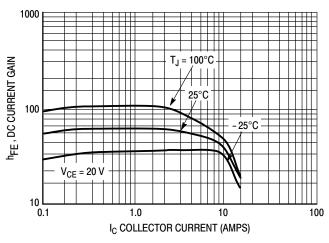
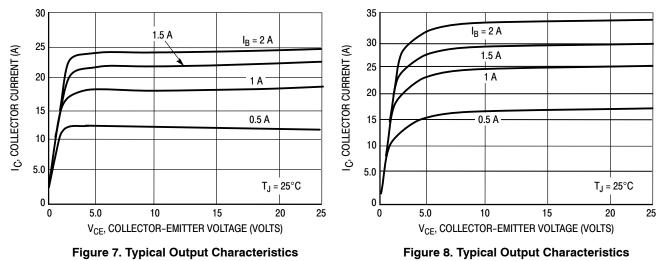


Figure 6. DC Current Gain, V<sub>CE</sub> = 5 V

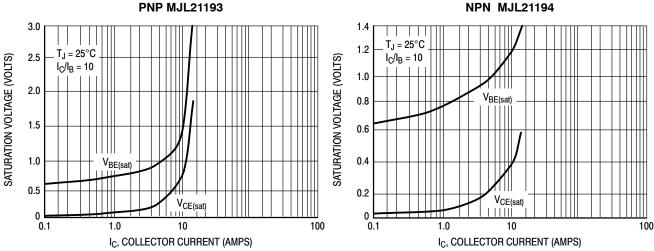
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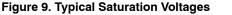


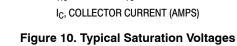
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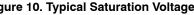
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### **TYPICAL CHARACTERISTICS**









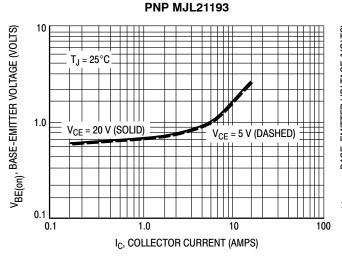


Figure 11. Typical Base-Emitter Voltage

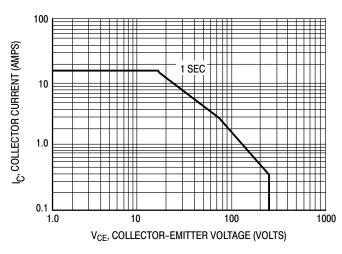


Figure 13. Active Region Safe Operating Area

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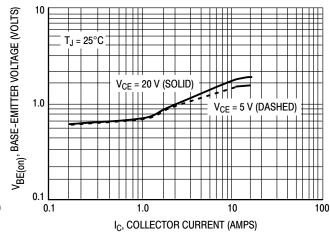


Figure 12. Typical Base-Emitter Voltage

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on  $T_{J(pk)} = 150^{\circ}$ C; T<sub>C</sub> is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

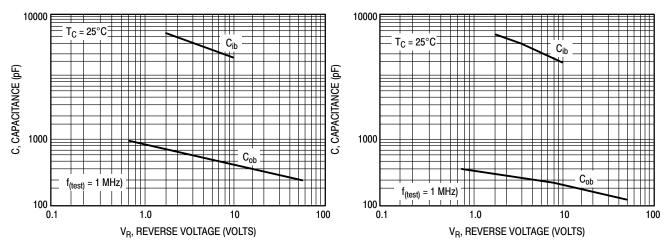


Figure 14. MJL21193 Typical Capacitance

Figure 15. MJL21194 Typical Capacitance

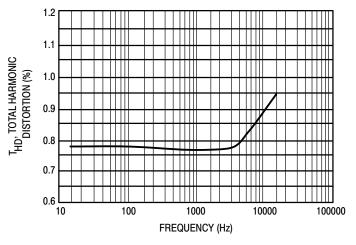


Figure 16. Typical Total Harmonic Distortion

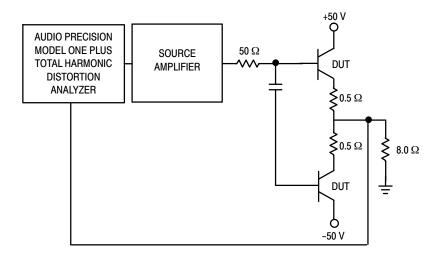
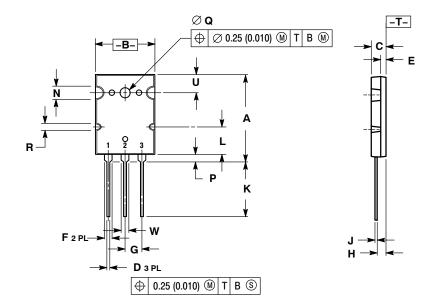


Figure 17. Total Harmonic Distortion Test Circuit

### PACKAGE DIMENSIONS

TO-3BPL (TO-264) CASE 340G-02 ISSUE J



	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	28.0	29.0	1.102	1.142	
в	19.3	20.3	0.760	0.800	
С	4.7	5.3	0.185	0.209	
D	0.93	1.48	0.037	0.058	
E	1.9	2.1	0.075	0.083	
F	2.2	2.4	0.087	0.102	
G	5.45 BSC		0.215 BSC		
н	2.6	3.0	0.102	0.118	
J	0.43	0.78	0.017	0.031	
к	17.6	18.8	0.693	0.740	
L	11.2 REF		0.411 REF		
Ν	4.35 REF		0.172 REF		
Р	2.2	2.6	0.087	0.102	
Q	3.1	3.5	0.122	0.137	
R	2.25 REF		0.089 REF		
U	6.3	6.3 REF		0.248 REF	
w	2.8	3.2	0.110	0.125	

 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.

STYLE 2: PIN 1. BASE 2. COLLECTOR

NOTES

3. EMITTER

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